

**AMENDMENTS TO THE SPECIFICATION**

Please replace paragraph [00026] with the following amended paragraph:

5 In a second embodiment of the present invention method, a surface treatment is performed after the gate insulating layer 44 is deposited. Therefore, the microcrystalline silicon layer 46 is deposited after the gate insulating layer 44 is treated. This is because the microcrystalline silicon layer 46 will be formed favorably if the interface between the gate insulating layer 44 and the microcrystalline silicon layer 46 contains more oxygen-containing molecules. In 10 this embodiment, a nitrous oxide ( $N_2O$ ) plasma treatment is performed, which results in the gate insulating layer 44 having stronger oxygen ~~binding~~ bonding with the subsequently formed microcrystalline silicon layer 46 and a stable interface of the gate insulating layer 44 and the microcrystalline silicon layer 46. In addition, the surface treatment process can be an oxygen-containing plasma 15 treatment that also provides stronger oxygen ~~binding~~ bonding between the gate insulating layer 44 and the microcrystalline silicon layer 46. The oxygen-containing gas of the oxygen-containing plasma process comprises nitric oxide (NO), nitrous oxide ( $N_2O$ ), nitrogen dioxide ( $NO_2$ ), hydrogen peroxide ( $H_2O_2$ ), oxygen ( $O_2$ ), ozone ( $O_3$ ), or tetra-ethyl-ortho-silicate (TEOS).

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